

40V N-Channel MOSFET

Applications:

- Power Supply
- DC-DC Converters

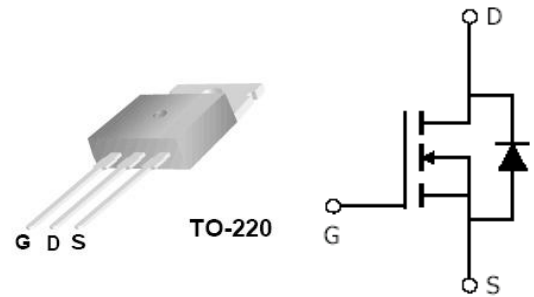
V_{DSS}	$R_{DS(ON)}$ (Max)	I_D^a
40 V	3.0 m Ω	260A

Features:

- Lead Free
- Low $R_{DS(ON)}$ to Minimize Conductive Loss
- Low Gate Charge for Fast Switching Application
- Optimized $B_{V_{DSS}}$ Capability

Ordering Information

Part Number	Package	Brand
MXP4003CTS	TO220	MXP



Absolute Maximum Ratings

$T_c=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	40	V
I_D^a	Continuous Drain Current ($T_c=25^\circ\text{C}$)	260	A
I_{DM}	Pulsed Drain Current @ $V_G=10\text{V}$	1040	
P_D	Power Dissipation	300	W
	Derating Factor above 25°C	2	W/ $^\circ\text{C}$
E_{AS}	Single Pulse Avalanche Energy (L=1mH)	1546	mJ
T_J and T_{STG}	Operating Junction and Storage Temperature Range	-55 to 175	$^\circ\text{C}$

a. Calculated continuous current based upon maximum allowable junction temperature, $+175^\circ\text{C}$. Package limitation current is 80A.

OFF Characteristics

$T_J=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	40			V	$V_{GS}=0\text{V}$, $I_D=250\mu\text{A}$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=32\text{V}$, $V_{GS}=0\text{V}$
				100		$V_{DS}=32\text{V}$, $V_{GS}=0\text{V}$ $T_J=125^\circ\text{C}$

I _{GSS}	Gate-to-Source Forward Leakage			100	nA	V _{GS} =+20V
	Gate-to-Source Reverse Leakage			100		V _{GS} = -20V

ON Characteristics

T_J=25°C unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
R _{DS(ON)}	Static Drain-to-Source On-Resistance		2.7	3	mΩ	V _{GS} = 10V, I _D =24A
V _{GS(TH)}	Gate Threshold Voltage	2		4	V	V _{DS} =V _{GS} , I _D =250μA

Dynamic Characteristics

Essentially independent of operating temperature

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
C _{ISS}	Input Capacitance		6144		pF	V _{GS} =0V, V _{DS} =25V, f=1.0MHz
C _{OSS}	Output Capacitance		2378			
C _{RSS}	Reverse Transfer Capacitance		660			
Q _g	Total Gate Charge		71		nC	V _{DD} =20V, I _D =30A, V _G =10V
Q _{gs}	Gate-to-Source Charge		24			
Q _{gd}	Gate-to-Drain ("Miller") Charge		35			
t _{d(on)}	Turn-on Delay Time		18		ns	V _{DD} =20V, I _D =63A, V _G =10V, R _G =4.7Ω
t _r	Rise Time		160			
t _{d(off)}	Turn-off Delay Time		42			
t _f	Fall Time		61			

Source-Drain Diode Characteristics

T_c=25°C unless otherwise specified

Symbol	Parameter	Min	Typ	Max	Units	Test Conditions
V _{SD}	Diode Forward Voltage			1.2	V	I _S =24A, V _{GS} =0V
T _{rr}	Reverse Recovery Time		78		ns	I _S =30A, di/dt = 100A/μs
Q _{rr}	Reverse Recovery Charge		148		nC	

Thermal Resistance

Symbol	Parameter	Min	Typ	Max	Unit	Test Conditions
R _{θJC}	Junction-to-Case	-	-	0.95	°C/W	Water cooled heatsink, P _D adjusted for a peak junction Temperature of 175°C

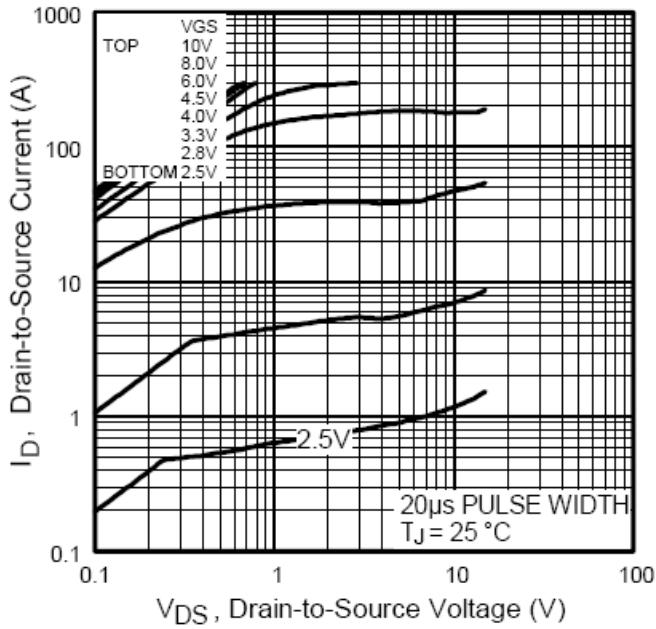


Fig 1. Typical Output Characteristics

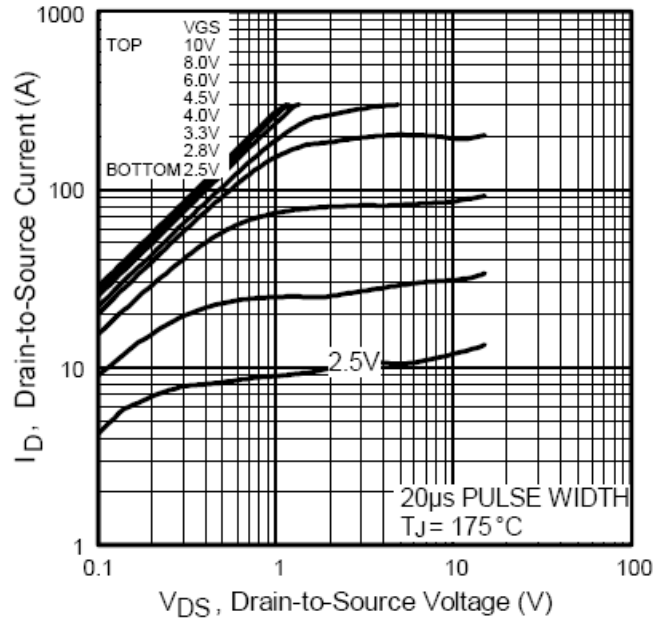


Fig 2. Typical Output Characteristics

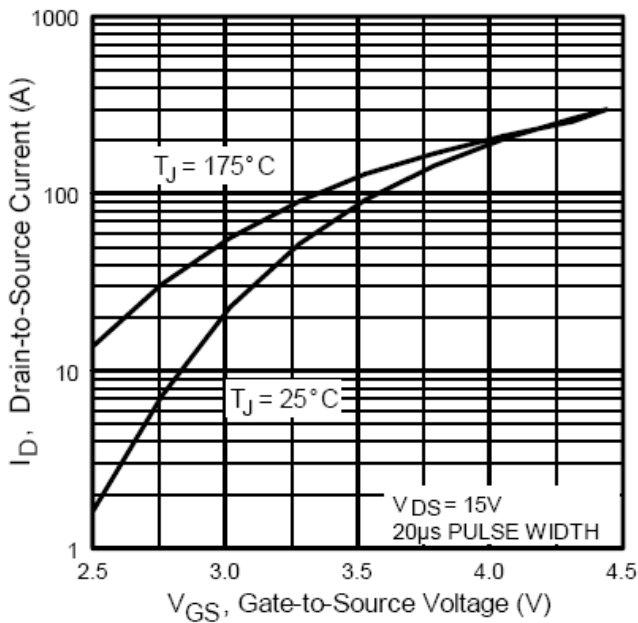


Fig 3. Typical Transfer Characteristics

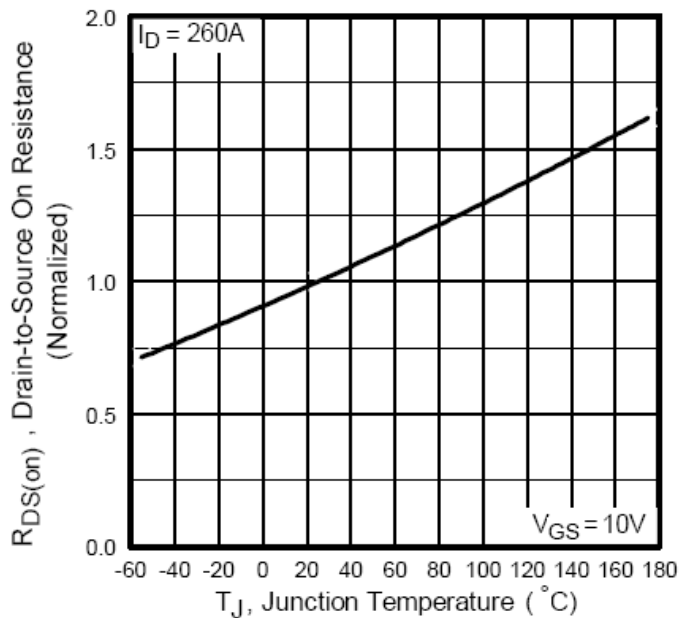


Fig 4. Normalized On-Resistance Vs. Temperature

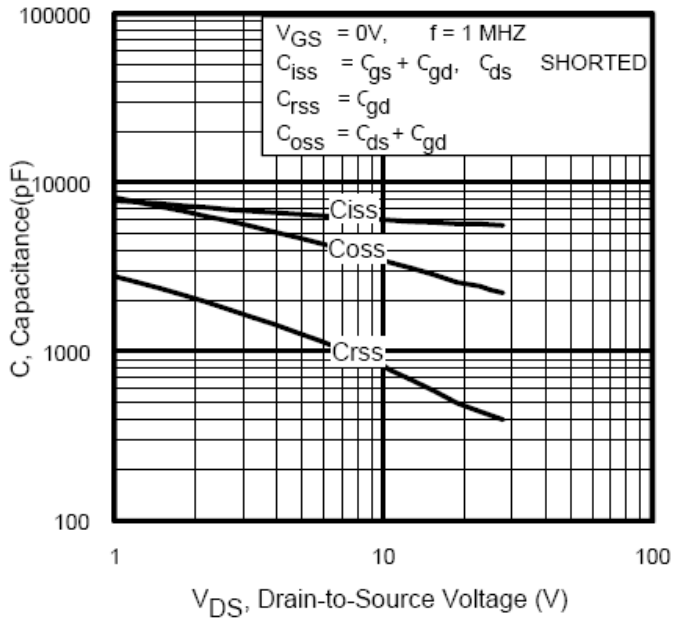


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

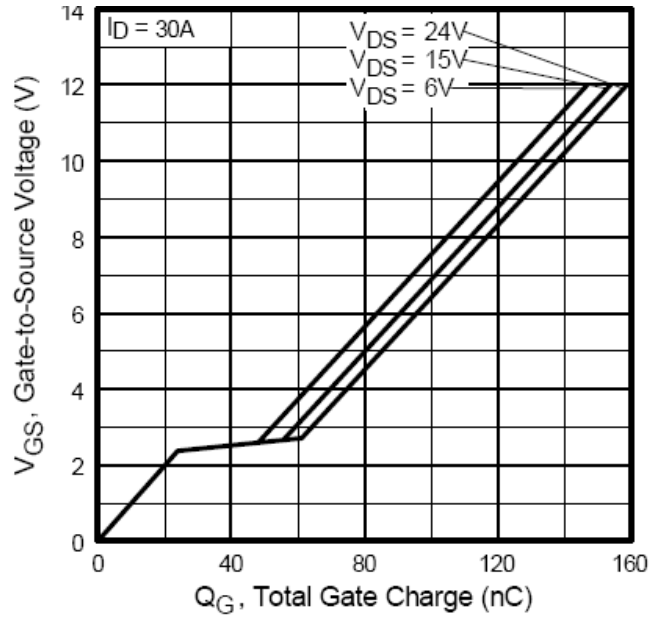


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

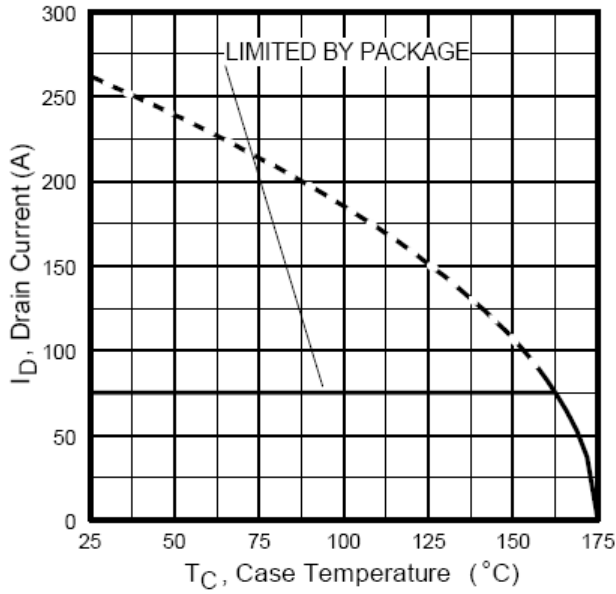


Fig 7. Maximum Drain Current Vs. Case Temperature

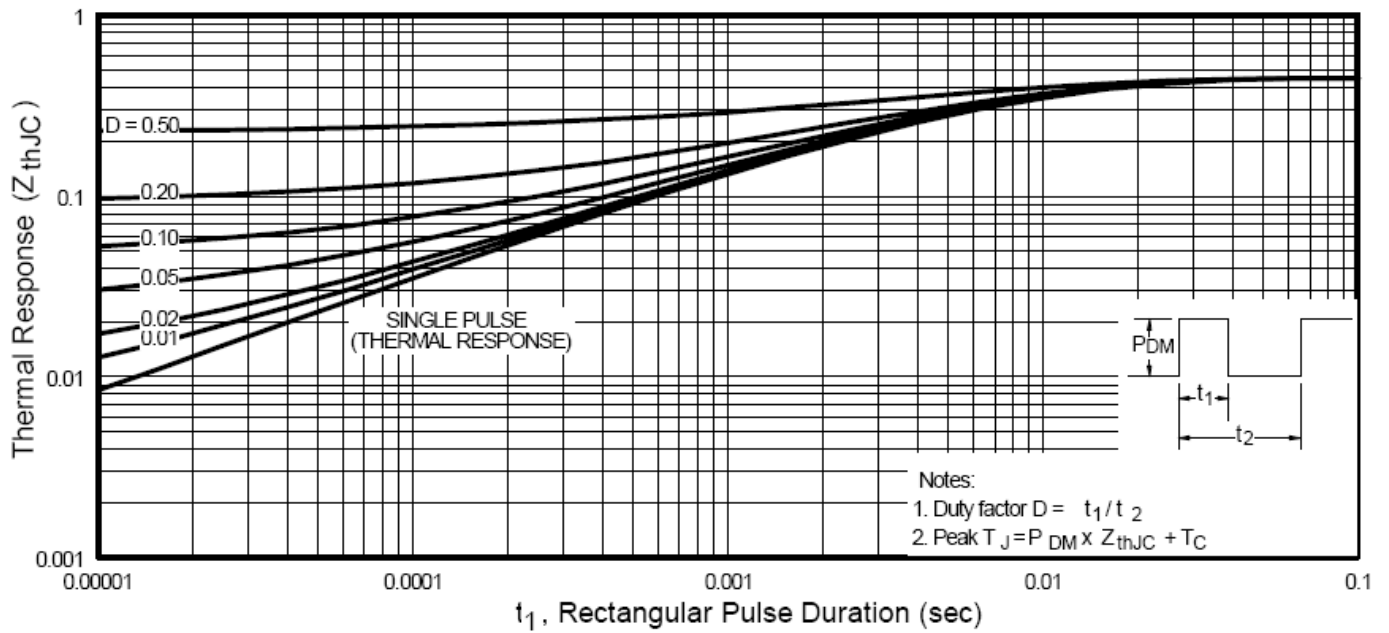
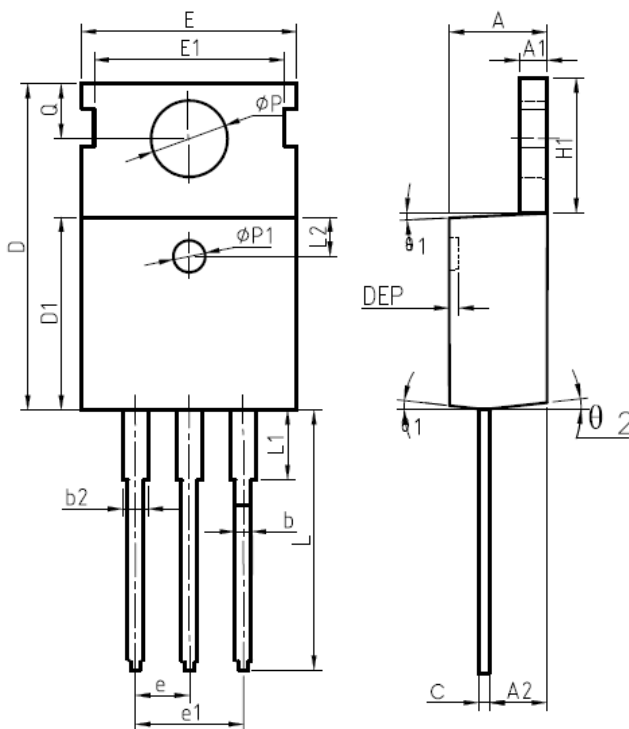


Fig 8 . Maximum Effective Transient Thermal Impedance, Junction-to-Case

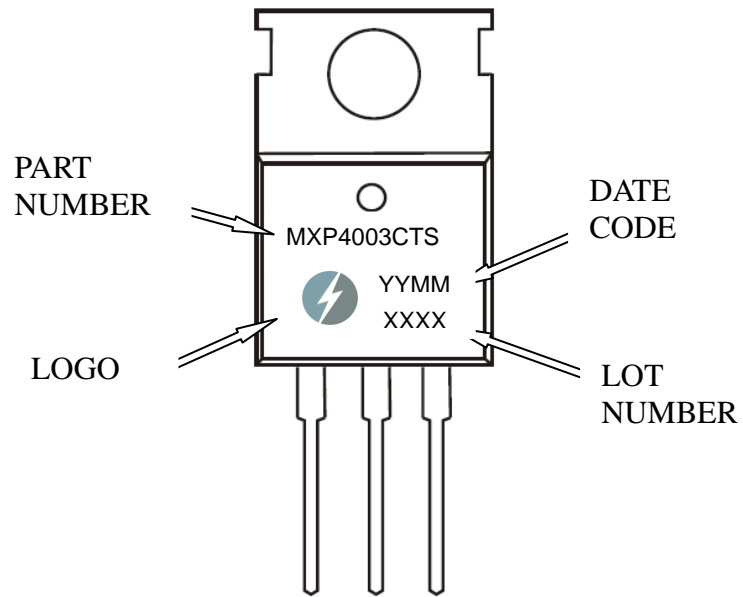
Package Outline
TO-220



COMMON DIMENSIONS

SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.40	4.57	4.70	0.173	0.180	0.185
A1	1.27	-	1.37	0.050	-	0.054
A2	2.35	2.40	2.50	0.091	0.094	0.098
b	0.77	-	0.90	0.030	-	0.035
b2	1.23	-	1.36	0.048	-	0.054
c	0.48	-	0.56	0.019	-	0.022
D	15.40	15.60	15.80	0.606	0.614	0.622
D1	9.00	9.10	9.20	0.354	0.358	0.362
DEP	0.05	0.10	0.20	0.002	0.004	0.008
E	9.70	9.90	10.20	0.382	0.389	0.402
E1	-	8.70	-	-	0.343	-
E2	9.80	10.00	10.20	0.386	0.394	0.401
ϕP	1.40	1.50	1.60	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.40	6.50	6.60	0.252	0.256	0.260
L	12.75	-	13.17	0.502	-	0.519
L1	-	-	3.95	-	-	0.156
L2	2.50REF			0.098REF		
$\phi P1$	3.50 $\text{\textcircled{Q}}$	3.60	3.63	0.137	0.142	0.143
Q	2.73	2.80	2.87	0.107	0.110	0.116
θ_1	5°	7°	9°	5°	7°	9°
θ_2	1°	3°	5°	1°	3°	5°

Part Marking Information
TO-220



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